

## HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	<b>2 x 15 A</b>
$V_{RRM}$	<b>60 V</b>
$T_j(\text{max})$	<b>150°C</b>
$V_F(\text{max})$	<b>0.75 V</b>

### FEATURES AND BENEFITS

- Negligible switching losses
- Low forward voltage drop
- Low capacitance
- High reverse avalanche surge capability.

### DESCRIPTION

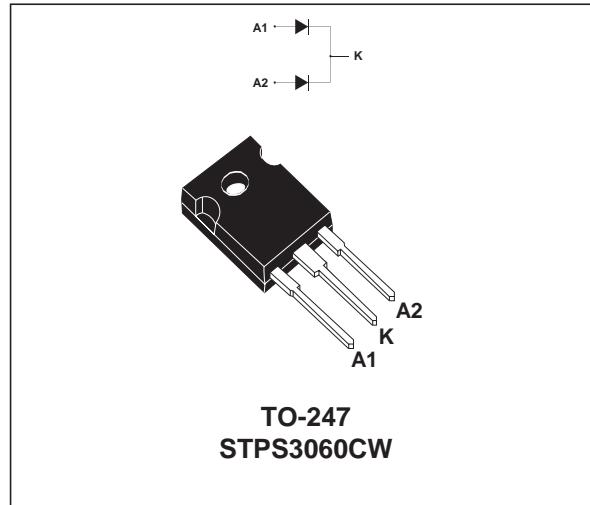
High voltage dual Schottky rectifier suited for switchmode power supplies and other power converters.

Packaged in TO-247, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses and low noise are required.

### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage			60	V
$I_{F(\text{RMS})}$	RMS forward current		Per diode	30	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$		Per diode Per device	15 30	A
$I_{FSM}$	Surge non repetitive forward current		Per diode	200	A
$I_{RRM}$	Repetitive peak reverse current	tp = 10 ms F=1kHz	Per diode	1	A
$I_{RSR}$	Non repetitive peak reverse current	tp = 100μs	Per diode	1	A
$T_{stg}$	Storage temperature range			- 65 to + 150	°C
$T_j$	Maximum operating junction temperature *			150	°C
$dV/dt$	Critical rate of rise of reverse voltage			1000	V/μs

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$  thermal runaway condition for a diode on its own heatsink



## STPS3060CW

### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode Total	1.5 0.8 °C/W
R <sub>th(c)</sub>		Coupling	0.1 °C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{\text{th(j-c)}}(\text{Per diode}) + P(\text{diode 2}) \times R_{\text{th(c)}}$$

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	Reverse leakage current	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			150	μA
		T <sub>j</sub> = 125°C				100	mA
V <sub>F</sub> *	Forward voltage drop	T <sub>j</sub> = 25°C	I <sub>F</sub> = 15 A			0.85	V
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 15 A		0.65	0.75	
		T <sub>j</sub> = 25°C	I <sub>F</sub> = 30 A			1.05	
		T <sub>j</sub> = 125°C	I <sub>F</sub> = 30 A		0.80	0.90	

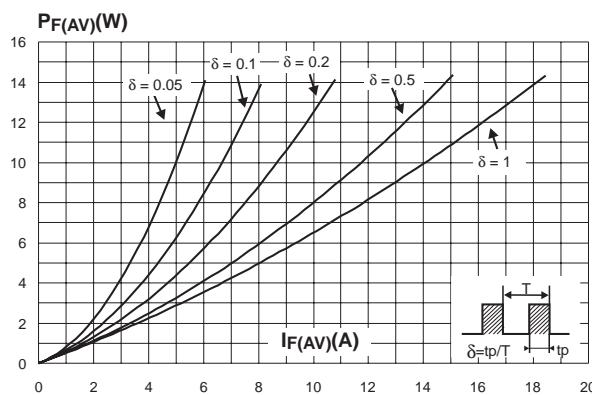
Pulse test: \* tp = 5ms, δ < 2%

\*\*tp = 380μs, δ < 2%

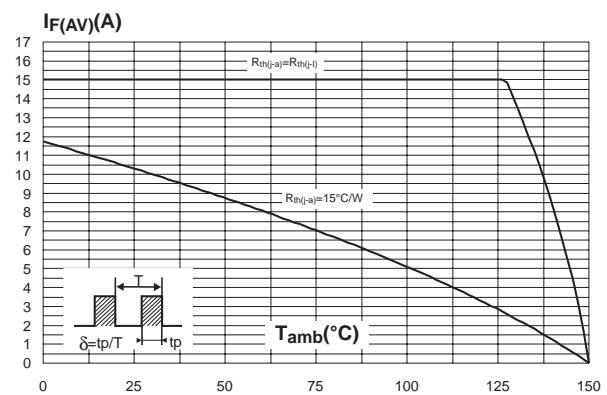
To evaluate the maximum conduction losses use the following equation :

$$P = 0.6 \times I_{F(\text{AV})} + 0.01 I_{F(\text{RMS})}^2$$

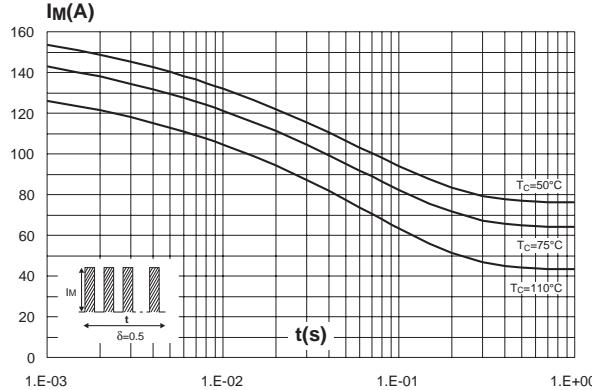
**Fig. 1:** Conduction losses versus average current (per diode).



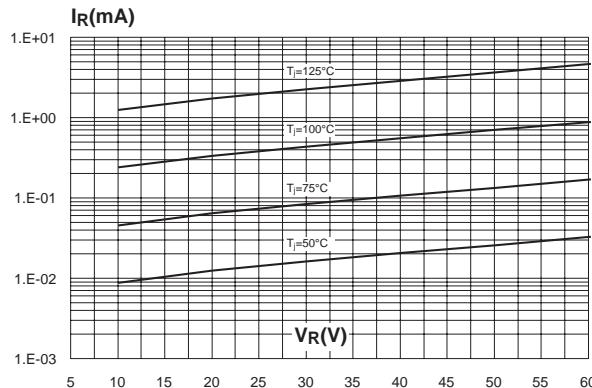
**Fig. 2:** Average forward current versus ambient temperature (δ=0.5, per diode).



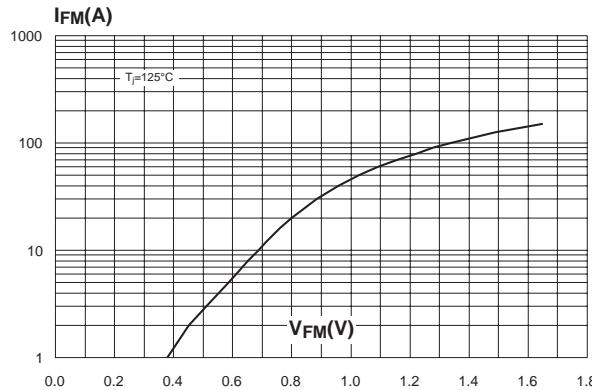
**Fig. 3:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



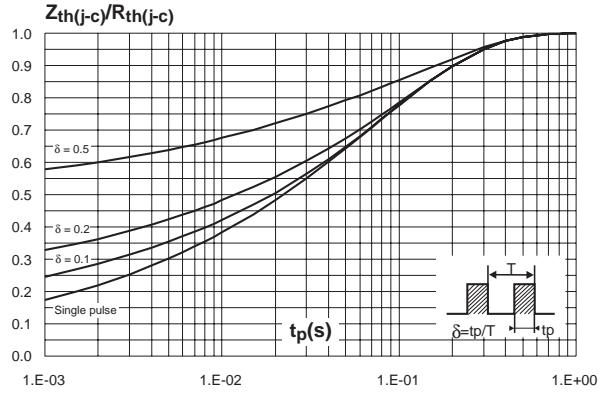
**Fig. 5:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



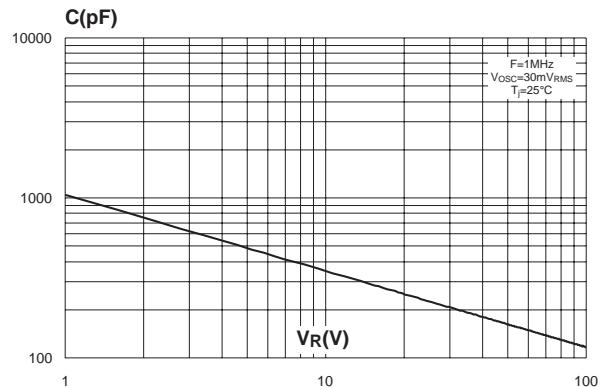
**Fig. 7:** Forward voltage drop versus forward current (maximum values, per diode).



**Fig. 4:** Relative variation of thermal impedance junction to case versus pulse duration.



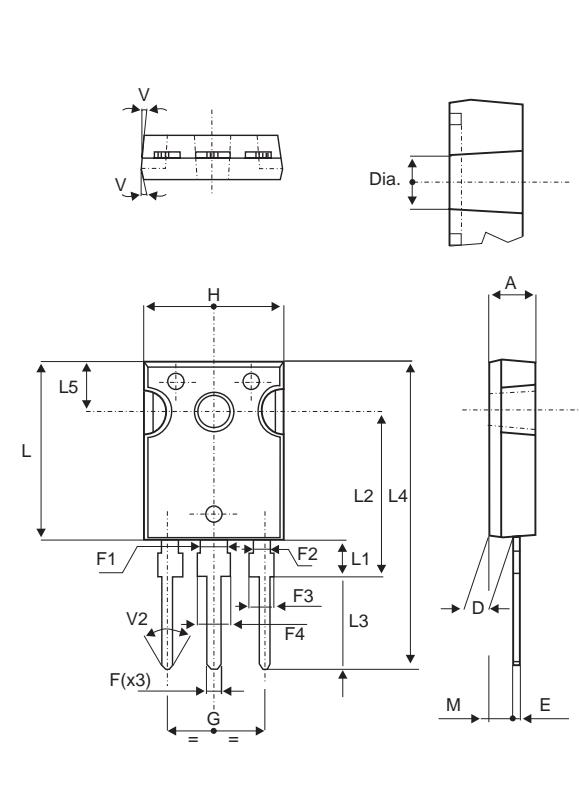
**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values, per diode).



## STPS3060CW

### PACKAGE MECHANICAL DATA

TO-247



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS3060CW	STPS3060CW	TO-247	4.4 g	50	Tube

- Epoxy meets UL94,V0

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